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MAY 20 2008

IN THE CLAIMS

Claims 1-16 (Canceled).

17 (Currently Amended). A transistor comprising:

a source region;

a drain region;

a plurality of nanotubes extending between said source and drain regions, said nanotubes having functionalized ends with attached functional groups, wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain region, said first functionalized ends attracted to said source region and not said drain region; and

a gate electrode over said nanotubes.

18 (Original). The transistor of claim 17 wherein said nanotubes are parallel to one another.

19 (Previously Presented). The transistor of claim 17 wherein said nanotubes are spaced equidistantly from one another.

Claims 20 and 21 (Canceled).

22 (Original). The transistor of claim 17 wherein said nanotubes are capless.

23 (Currently Amended). A transistor comprising:

a source region;

a drain region;

a plurality of open ended nanotubes extending between said source and drain regions, wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain region, said first functionalized ends attracted to said source region and not said drain region; and

a gate electrode over said nanotubes.

24 (Previously Presented). The transistor of claim 23 wherein said nanotubes are parallel to one another.

25 (Previously Presented). The transistor of claim 23 wherein said nanotubes are spaced equidistantly from one another.

26 (Previously Presented). The transistor of claim 23 wherein said nanotubes have functionalized ends.

Claim 27 (Canceled).

28 (Previously Presented). A transistor comprising:  
a source region;  
a drain region;  
a plurality of nanotubes extending between source and drain regions, each nanotubes including two opposed ends, the opposed ends of each nanotube having different functional groups attached to the opposed ends.

29 (Previously Presented). The transistor of claim 28 wherein said nanotubes are parallel.

30 (Previously Presented). The transistor of claim 28 wherein said nanotubes are spaced equidistantly from one another.

31 (Previously Presented). The transistor of claim 28 wherein said nanotubes have opposed first functionalized ends coupled to said source region and second functionalized ends coupled to said drain regions, said first functionalized ends attracting to said source region and not said drain region.